

December 2007

FAN7311 LCD Backlight Inverter Drive IC

Features

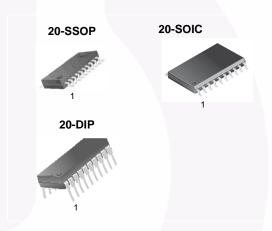
- High-Efficiency Single-Stage Power Conversion
- Wide Input Voltage Range: 5V to 25.5V
- Backlight Lamp Ballast and Soft Dimming
- Reduced Number of Required External Components
- Precision Voltage Reference Trimmed to 2%
- ZVS Full-Bridge Topology
- Soft-Start Capability
- PWM Control at Fixed Frequency
- Analog and Burst Dimming Function
- Programmable Striking Frequency
- Open-Lamp Protection
- Open-Lamp Regulation
- 20-Pin SSOP/SOIC/DIP

Applications

- LCD TV
- LCD Monitor

Description

The FAN7311 provides all the control functions for a series parallel resonant converter as well as a pulse width modulation (PWM) controller to develop a supply voltage. Typical operating frequency range is between 30kHz and 250kHz, depending on the cold cathode fluorescent lamp (CCFL) and the transformer's characteristics. FAN7311 uses a new patented phase-shift control.



Ordering Information

Part Number	Package	Operating Temperature Range	Packing Method
FAN7311G	20-SSOP		Rail
FAN7311GX	20-SSOP		Tape & Reel
FAN7311M	20-SOIC	-25°C to 85°C	Rail
FAN7311MX	20-SOIC		Tape & Reel
FAN7311N	20-DIP		Rail



All packages are lead free per JEDEC: J-STD-020B standard.

Protected by U.S. Patent: 5,652,479; 7,158,390.

Internal Block Diagram

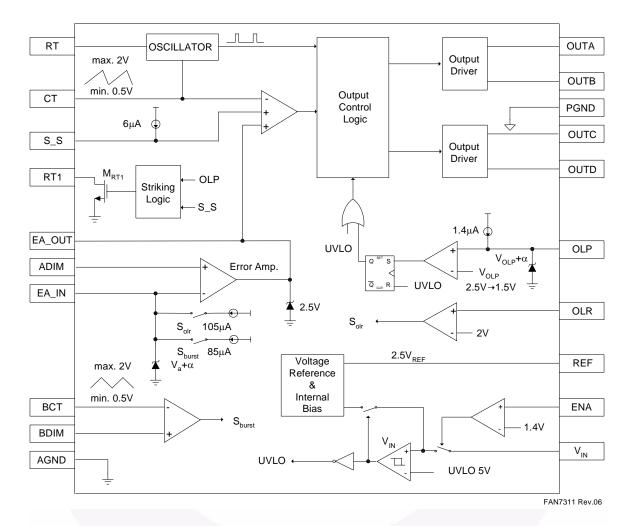


Figure 1. Functional Block Diagram of FAN7311

Pin Assignments

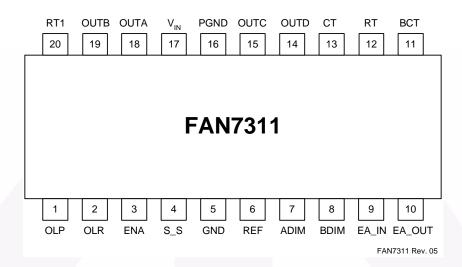


Figure 2. Pin Configuration (Top View)

Pin Definitions

Pin#	Name	Description	Pin#	Name	Description
1	OLP	Open-Lamp Protection	11	BCT	Burst Dimming Timing Capacitor
2	OLR	Open-Lamp Regulation	12	RT	Timing Resistor
3	ENA	Enable Input	13	CT	Timing Capacitor
4	S_S	Soft-Start	14	OUTD	NMOSFET Drive Output D
5	GND	Analog Ground	15	OUTC	PMOSFET Drive Output C
6	REF	2.5V Reference Voltage	16	PGND	Power Ground
7	ADIM	Analog Dimming Input	17	V _{IN}	Supply Voltage
8	BDIM	Burst Dimming Input	18	OUTA	PMOSFET Drive Output A
9	EA_IN	Error Amplifier Input	19	OUTB	NMOSFET Drive Output B
10	EA_OUT	Error Amplifier Output	20	RT1	Striking Frequency Resistor

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Characteristics	Min.	Max.	Unit	
V _{IN}	Supply Voltage		5.0	25.5	V
T _A	Operating Temperature Range		-25	+85	°C
T _J	Junction Temperature			+150	°C
T _{STG}	Storage Temperature Range		-65	+150	°C
Α	Thermal Resistance Junction-to-Ambient (still air) ⁽¹⁾	20-SSOP		112	°C/W
θ_{JA}	Thermal Resistance Sunction-to-Ambient (still all)	20-SOIC		90	C/VV
D	Power Dissipation	20-SSOP		1.1	W
P _D	Fower Dissipation	20-SOIC		1.4	VV

Notes:

1. Thermal resistance test board size: 76.2 • 114.3 • 1.6mm (1S0P). JEDEC standard: JESD51-2, JESD51-3.

Electrical Characteristics

For typical values, T_A =25°C and V_{IN} =12V. For minimum and maximum values, T_A is the operating ambient temperature range with -25°C $\leq T_A \leq 85$ °C and $5V \leq V_{IN} \leq 25.5V$, unless otherwise specified. Specifications from -25°C to 85°C are guaranteed by design based on final characterization results.

Symbol	Characteristics	Test Condition	Min.	Тур.	Max.	Unit
REFEREN	ICE SECTION (Recommend X7R Capacit	or)				
ΔV_{ref}	Line Regulation	$5 \leq V_{IN} \leq 25.5V$		2	25	mV
V25	2.5V Regulation Voltage		2.45	2.50	2.55	V
OSCILLA.	TOR SECTION (MAIN)				•	
f _{osc}	Oscillation Frequency	$T_A = 25$ °C, CT = 270pF, RT = 18k Ω	110.4	115.0	119.6	kHz
		$CT = 270pF, RT = 18k\Omega$	108	115	122	
V _{cth}	CT High Voltage			2.0		V
V _{ctl}	CT Low Voltage			0.5		V
OSCILLA.	TOR SECTION (BURST)					
f _{oscb}	Oscillation Frequency	$T_A = 25$ °C, $C_{tb} = 10$ nF, RT=18k Ω	209.25	225.00	240.75	Hz
		$C_{tb} = 10$ nF, RT=18k Ω	206.25	225.00	241.75	
V_{bcth}	BCT High Voltage			2		V
V_{bctl}	BCT Low Voltage			0.5		V
ERROR A	MP SECTION					
A_{V}	Open-Loop Gain ⁽³⁾			80		dB
G_BW	Unit Gain Bandwidth ⁽³⁾			1.5		MHz
V _{eh}	Feedback Output High Voltage	EA_IN = 0V	2.00	2.27	2.54	>
I _{sin}	Output Sink Current	EA_OUT = 1.5V			-1	mA
I _{sur}	Output Source Current	EA_OUT = 1.5V	1			mA
l _{olr}	EA_IN Driving Current on OLR		75	105	135	μA
I _{burst}	EA_IN Driving Current on Burst Dimming		61	85	109	μA
V _{fbh}	Feedback High Voltage on Burst Dimming	$R(EA_IN) = 60k\Omega$	V _a +0.1	V _a +0.4	V _a +0.7	V
SOFT-STA	ART SECTION					
I _{SS}	Soft-Start Current	S_S=1V	4	6	8	μΑ
V _{ssh}	Soft-Start Clamping Voltage ⁽³⁾			4		V
PROTECT	TION SECTION					
V _{olp0}	Open-Lamp Protection Voltage 0	Start at open lamp	2.2	2.5	2.8	V
V _{olp1}	Open-Lamp Protection Voltage 1	Normal -> open lamp	1.3	1.5	1.7	V
V _{olr}	Open-Lamp Regulation Voltage		1.75	2.00	2.25	V
l _{olp}	Open-Lamp Protection Charging Current		0.7	1.4	2.1	μΑ
	OLTAGE LOCKOUT SECTION				-	
V _{th}	Start Threshold Voltage				5	V
I _{st}	Start-up Current	$V_{IN} = V_{th}$ -0.2		130	180	μA
I _{op}	Operating Supply Current	V _{IN} = 12V		1.5	4.0	mA
I _{sb}	Stand-by Current	V _{IN} = 12V		200	370	μA

Note:

3. These parameters, although guaranteed, are not 100% tested in production.

Electrical Characteristics (Continued)

For typical values, T_A =25°C and V_{IN} =12V. For min. and max. values, T_A is the operating ambient temperature range with -25°C $\leq T_A \leq 85$ °C and $5V \leq V_{IN} \leq 25.5V$, unless otherwise specified. Specifications from -25°C to 85°C are guaranteed by design based on final characterization results.

Symbol	Characteristics	Test Condition	Min.	Тур.	Max.	Unit
ON/OFF S	ECTION					
V _{on}	On State Input Voltage		2		5	V
V _{off}	Off Stage Input Voltage				0.7	V
OUTPUT	SECTION					
V_{pdhv}	PMOS Gate High Voltage	V _{IN} = 12V		V_{IN}		V
V_{phlv}	PMOS Gate Low Voltage	V _{IN} = 12V	V _{IN} -10.5	V _{IN} -8.5	V _{IN} -6.5	V
V _{ndhv}	NMOS Gate Drive Voltage	V _{IN} = 12V	6.5	8.5	10.5	V
V _{ndhv}	NMOS Gate Drive Voltage	V _{IN} = 12V	/	0		V
V_{puv}	PMOS Gate Voltage With UVLO Activated	$V_{IN} = V_{th}-0.2$	V _{IN} -0.3			V
V _{nuv}	NMOS Gate Voltage With UVLO Activated	$V_{IN} = V_{th}$ -0.2			0.3	V
t _r	Rising Time ⁽⁴⁾	$V_{IN} = 12V, C_L=2nF$		200	500	ns
t _f	Falling Time ⁽⁴⁾	$V_{IN} = 12V, C_L=2nF$		200	500	ns
MAXIMUN	I / MINIMUM OVERLAP					
	Minimum Overlap Between Diagonal Switches ⁽⁴⁾	f _{osc} = 100kHz		0		%
	Maximum Overlap Between Diagonal Switches ⁽⁴⁾	f _{osc} = 100kHz		100		%
DELAY TI	ME					
	PDR_A/NDR_B ⁽⁴⁾	RT = 18kΩ		450		ns
	PDR_C/NDR_D ⁽⁴⁾	RT = 18kΩ		450		ns

Note:

4. These parameters, although guaranteed, are not 100% tested in production.

Function Description

UVLO: The under-voltage lockout circuit guarantees stable operation of the IC's control circuit by stopping and starting it as a function of the V_{IN} value. The UVLO circuit turns on the control circuit when V_{IN} exceeds 5V. When V_{IN} is lower than 5V, the IC's standby current is less than 200µA.

ENA: Applying voltage higher than 2V to the ENA pin enables operation of the IC. Applying voltage lower than 0.7V to the ENA pin disables operation of the inverter.

Soft-Start: The soft-start function requires that the S_S pin is connected through a capacitor to GND. A soft-start circuit ensures a gradual increase in the input and output power. The capacitor connected to the S_S pin determines the rate at which the duty ratio rises. It is charged by a $6\mu A$ current source.

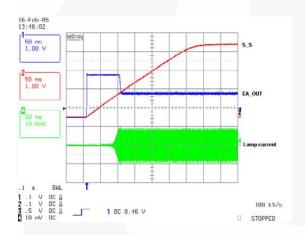


Figure 3. Soft-Start During Initial Operation

Main Oscillator: The timing capacitors (CTs) are charged by the reference current source, which is formed by the timing resistor (RT). The timing resistor's voltage is regulated at 1.25V. The sawtooth waveform charges up to 2V. Once this voltage is reached, the capacitors begin discharging down to 0.5V. Next, the timing capacitors start charging again and a new switching cycle begins. The main frequency can be programmed by adjusting the RT and CT values. The main frequency can be calculated as shown below.

$$f_{op} = \frac{19}{32 \cdot RT \cdot CT} \tag{1}$$

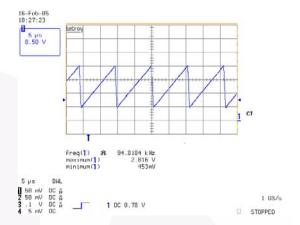


Figure 4. Main Oscillator Waveform

Burst Oscillator & Burst Dimming: The timing capacitors (BCTs) are charged by the reference current source, which is formed by the timing resistor (RT). The timing resistor's voltage is regulated at 1.25V. The sawtooth waveform charges up to 2V. Once this voltage is reached, the capacitors begin discharging down to 0.5V. Next, the timing capacitors start charging again and a new switching cycle begins. The burst dimming frequency can be programmed by adjusting the RT and BCT values. The burst dimming frequency can be calculated as shown in Equation 2.

$$f_{burst} = \frac{3.75}{96 \cdot RT \cdot CT} \tag{2}$$

To avoid visible flicker, the burst dimming frequency should be greater than 120Hz.

By comparing the input of BDIM pin with the 0.5~2V triangular wave of the burst oscillator, the PWM pulses for burst dimming. The PWM pulse controls EA_OUT's voltage by summing 85µA into the EA_IN pin.

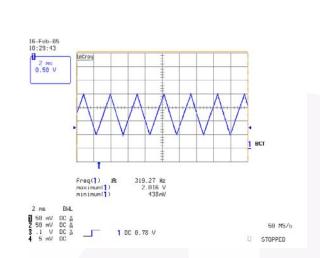


Figure 5. Burst Oscillator Waveform

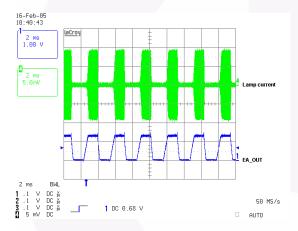


Figure 6. Burst Dimming

Open-Lamp Regulation and Open-Lamp Protection: It is necessary to suspend power stage operation if an open lamp occurs, because the power stage has high gain. When a voltage higher than 2V is applied to the OLR pin, the part enters regulation mode and controls the EA_OUT voltage. This limits the lamp voltage by summing 105μA into the feedback node. At the same time, the OLP capacitor, connected to the OLP pin, is charged by the 1.4μA internal current source. Once it reaches 2.5V, the IC shuts down and all output is high.

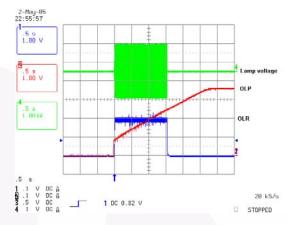


Figure 7. OLR Voltage During Striking Mode

Output Drives: The four output drives are designed so that switches A and B, C and D never turn on simultaneously. The OUTA-OUTB pair is intended to drive one half-bridge in the external power stage. The OUTC-OUTD pair drives the other half-bridge.

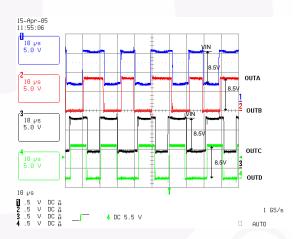


Figure 8. Phase-Shift Control Waveforms

Timing Diagram

The FAN7311 uses the improved phase-shift control full-bridge to drive CCFL. As a result, the temperature difference between the left and the right leg is almost zero. The detail timing is shown below.

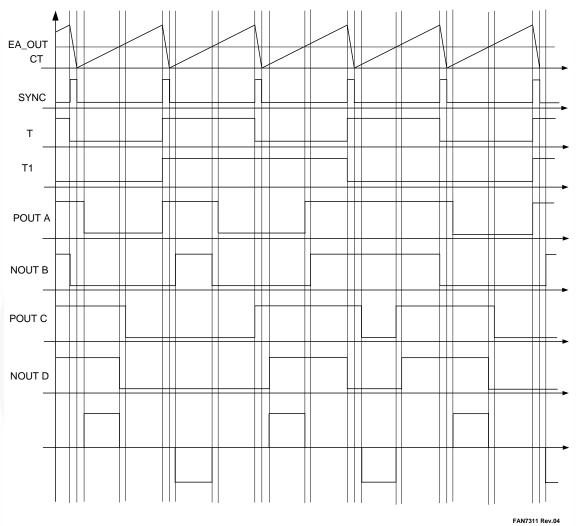


Figure 9. Phase-Shift Control Waveforms

Typical Application Circuits

Application	Lamps	Input Voltage
19-inch LCD Monitor	4	13V

1. Schematic

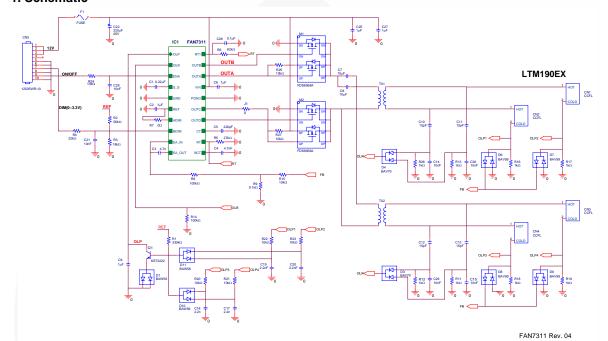


Figure 10. Typical Application Circuit

2. Transformer Schematic Diagram

- Supported by Namyang electronics (http://www.namyangelec.co.kr)

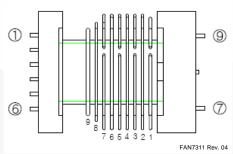


Figure 11. Transformer Schematic

3. Core & Bobbin

Core: EFD2124Material: PL7Bobbin: EFE2124

4. Winding Specification

Pin No.	Wire	Turns	Inductance	Leakage Inductance	Remarks
5> 2	1 UEW 0.45 φ	19	115 µH	21.5µH	1KHz, 1V
7> 9	1 UEW 0.04 φ	2300	1.5 H	280mH	1KHz, 1V

5. BOM of the Application Circuit

Part Ref.	Value	Description / Vendor	Part Ref.	Value	Description / Vendor
	Fus	se	C5	220pF	50V 1608 J
F1	24V 3A	Fuse	C6	1µF	50V 2012 K
	Resistor	(SMD)	C7	10µF	16V 3216
R1	330kΩ	1608 J	C8	10μF	16V 3216
R2	56kΩ	1608 F	C9	1µF	16V 1608 K
R3	18kΩ	1608 F	C10	15pF	3KV 3216
R4	22kΩ	1608 F	C11	15pF	3KV 3216
R5	27kΩ	1608 F	C12	15pF	3KV 3216
R6	82kΩ	1608 F	C13	15pF	3KV 3216
R8	100kΩ	1608 F	C14	10nF	50V 1608 K
R9	9.1kΩ	1608 F	C15	10nF	50V 1608 K
R11	1kΩ	1608 F	C17	2.2nF	50V 1608 Z
R12	1kΩ	1608 F	C18	2.2nF	50V 1608 Z
R13	1kΩ	1608 F	C19	2.2nF	50V 1608 Z
R14	100kΩ	1608 F	C20	2.2nF	50V 1608 Z
R15	10kΩ	1608 F	C21	10nF	50V 1608 Z
R16	1kΩ	1608 F	C25	1µF	50V 2012 K
R17	1kΩ	1608 F	C26	0.1µF	16V 1608 K
R18	1kΩ	1608 F	C27	1µF	50V 2012 K
R19	1kΩ	1608 F	C28	10nF	50V 1608 Z
R20	10kΩ	1608 J	C29	10nF	50V 1608 K
R21	10kΩ	1608 J	C30	10nF	50V 1608 K
R22	10kΩ	1608 J	Diode / TR (SMD)		
R23	10kΩ	1608 J	D1	BAW56	Fairchild Semiconductor
R24	10kΩ	1608 J	D3	BAV70	Fairchild Semiconductor
R25	10kΩ	1608 J	D4	BAV70	Fairchild Semiconductor
R26	1kΩ	1608 F	D6	BAV99	Fairchild Semiconductor
R27	10kΩ	1608 J	D7	BAV99	Fairchild Semiconductor
	Capacito	r (SMD)	D8	BAV99	Fairchild Semiconductor
C1	0.22µF	16V 1608 K	D9	BAV99	Fairchild Semiconductor
C2	1µF	50V 2012 K	D10	BAW56	Fairchild Semiconductor
C3	4.7nF	50V 1608 K	D11	BAW56	Fairchild Semiconductor
C4	4.7nF	50V 1608 K	Q1	KST2222	Fairchild Semiconductor
	Electrolytic	capacitor		Wafer (S	SMD)
C22	220µF	25V	CN1	35001WR-02A	
MOSFET (SMD)		CN2	35001WR-02A		
M1	FDS8958A	Fairchild Semiconductor	CN3	35001WR-02A	
M2	FDS8958A	Fairchild Semiconductor	CN4	35001WR-02A	
	Transform	er (SMD)	CN5	12505WR-10	
TX1	EFD2124	Supported by Namy	rang alaatran	ice (http://www.s	amyangolog oo kr)
TX2	EFD2124	Supported by Namy	any electron	ics (nith://www.r	iamyangelec.co.kr)

Mechanical Dimensions

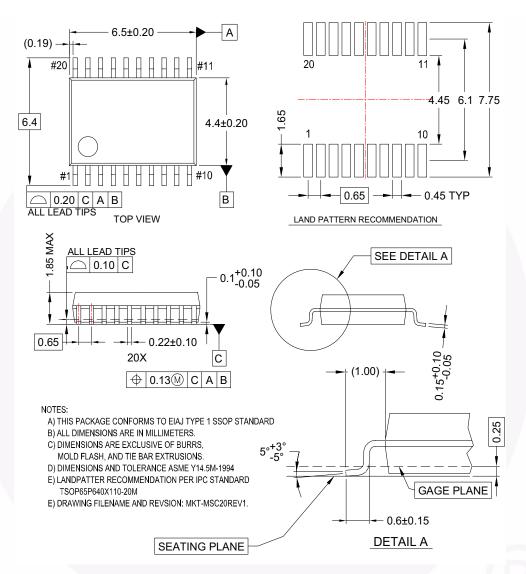


Figure 12. 20-Lead Shrink Small Outline Package (SSOP)

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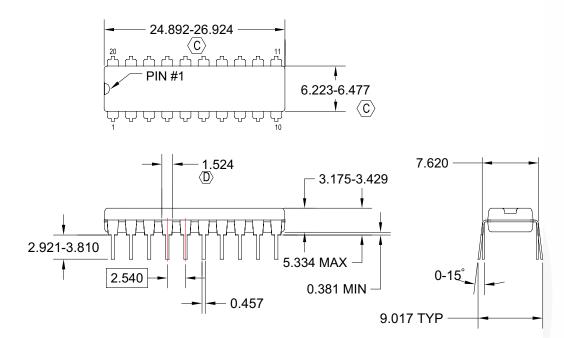
Mechanical Dimensions (Continued) 13.00 12.60 11.43 В 9.50 10.65 7.60 10.00 7.40 0.65 0.51 PIN ONE 1.27 0.35 INDICATOR ⊕ 0.25 M C B A LAND PATTERN RECOMMENDATION 2.65 MAX SEE DETAIL A 0.33 С 0.20 □ 0.10 C 0.30 0.10 0.75 X 45° SEATING PLANE 0.25 NOTES: UNLESS OTHERWISE SPECIFIED (R0.10) A) THIS PACKAGE CONFORMS TO JEDEC **GAGE PLANE** MS-013, VARIATION AC, ISSUE E (R0.10) B) ALL DIMENSIONS ARE IN MILLIMETERS. 0.25 C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS. D) CONFORMS TO ASME Y14.5M-1994 1.27 0.40 SEATING PLANE E) LANDPATTERN STANDARD: SOIC127P1030X265-20L -(1.40)F) DRAWING FILENAME: MKT-M20BREV3 DETAIL A

Figure 13. 20-Lead Small Outline Integrated Circuit (SOIC)

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 - B. ALL DIMENSIONS ARE IN MILLIMETERS
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- (D) DOES NOT INCLUDE DAMBAR PROTRUSIONS. DAMBAR PROTRUSIONS SHALL NOT EXCEED
- E. DRAWING FILE NAME: N20SREV1

Figure 14. 20-Lead Dual In-Line Package (DIP)

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